5 Output 1.8V HCSL Fanout Buffer with Zo = 100ohms

9DBV0541

DATASHEET

Description

The 9DBV0541 is a member of IDT's Full-Featured PCIe family. The device has 5 output enables for clock management, and 3 selectable SMBus addresses. It has integrated terminations for direct connection to 100ohm transmission lines.

Recommended Application

PCIe Gen1–3 clock distribution in Storage, Networking, Computing, Consumer

Output Features

- Five 1–200MHz Low-Power (LP) HCSL DIF pairs with Zo = 100 Ω
- Easy AC-coupling to other logic families, see IDT application note <u>AN-891</u>

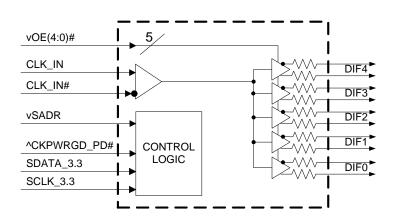
Key Specifications

- Additive cycle-to-cycle jitter < 5ps
- Output-to-output skew < 50ps
- Additive phase jitter is < 100fs rms for PCIe Gen3
- Additive phase jitter < 300fs rms (12kHz–20MHz at 125MHz)

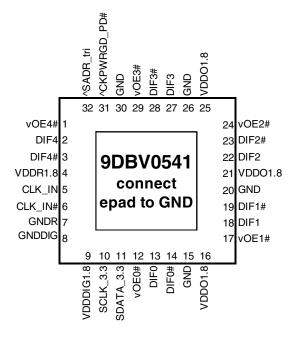
Features/Benefits

- 100 Ω direct connect; saves 20 resistors and 34mm² compared to standard HCSL
- 50mW typical power consumption; eliminates thermal concerns
- OE# pins; support DIF power management
- HCSL-compatible differential input; can be driven by common clock sources
- Spread spectrum compatible; allows EMI reduction
- SMBus-selectable features allow optimization to customer requirements
 - Slew rate for each output; allows tuning for various line length
 - Differential output amplitude; allows tuning for various application environments
- 1MHz to 200MHz operating frequency
- 3.3V tolerant SMBus interface works with legacy controllers
- Selectable SMBus addresses; multiple devices can easily share an SMBus segment
- Device contains default configuration; SMBus interface not required for device operation
- 32-pin 5 x 5 mm QFN; minimal board space

Block Diagram



Pin Configuration



32-pin QFN, 5 x 5 mm, 0.5mm pitch

 ^ prefix indicates internal 120kOhm pull-up resistor
 ^v prefix indicates internal 120kOhm pull-up AND pulldown resistor (biased to VDD/2)
 v prefix indicates internal 120kOhm pull-down resistor

SMBus Address Selection Table

	SADR	Address	+ Read/Write bit
State of SADR on first application of	0	1101011	X
CKPWRGD PD#	М	1101100	X
	1	1101101	x

Power Management Table

CKPWRGD PD#	CLK_IN	SMBus	OEx# Pin	DIF	Fx		
	CER_IN	OEx bit		True O/P	Comp. O/P		
0	Х	Х	Х	Low	Low		
1	Running	0	Х	Low	Low		
1	Running	1	0	Running	Running		
1	Running	1	1	Low	Low		

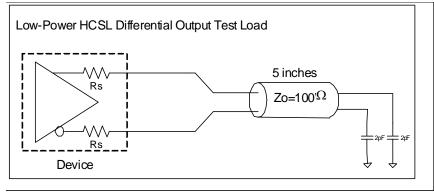
Power Connections

Pin Numb	ber	Description
VDD	GND	Description
4	7	Input receiver analog
9	8	Digital power
16, 21, 25	15,20,26,30	DIF outputs

Pin Descriptions

Pin#	Pin Name	Туре	Pin Description			
_			Active low input for enabling output 4. This pin has an internal 120kohm pull-down.			
1	vOE4#	IN	1 = disable outputs, 0 = enable outputs.			
2	DIF4	OUT	Differential true clock output.			
3	DIF4#	OUT	Differential complementary clock output.			
4	VDDR1.8	PWR	Power supply for differential input clock (receiver). This VDD should be treated as			
4	VDDR1.0	PVK	an analog power rail and filtered appropriately. Nominally 1.8V.			
5	CLK_IN	IN	rue input for differential reference clock.			
6	CLK_IN#	IN	Complementary input for differential reference clock.			
7	GNDR	GND	Analog ground pin for the differential input (receiver).			
8	GNDDIG	GND	Ground pin for digital circuitry.			
9	VDDDIG1.8	PWR	1.8V digital power (dirty power).			
10	SCLK_3.3	IN	Clock pin of SMBus circuitry, 3.3V tolerant.			
11	SDATA_3.3	I/O	Data pin for SMBus circuitry, 3.3V tolerant.			
10	vOE0#	INI	Active low input for enabling output 0. This pin has an internal 120kohm pull-down.			
12	VOE0#	IN	1 = disable outputs, 0 = enable outputs.			
13	DIF0	OUT	Differential true clock output.			
14	DIF0#	OUT	Differential complementary clock output.			
15	GND	GND	Ground pin.			
16	VDDO1.8	PWR	Power supply for outputs, nominally 1.8V.			
17	vOE1#	IN	Active low input for enabling output 1. This pin has an internal 120kohm pull-down.			
17	VOEI#	IIN	1 = disable outputs, 0 = enable outputs.			
18	DIF1	OUT	Differential true clock output.			
19	DIF1#	OUT	Differential complementary clock output.			
20	GND	GND	Ground pin.			
21	VDDO1.8	PWR	Power supply for outputs, nominally 1.8V.			
22	DIF2	OUT	Differential true clock output.			
23	DIF2#	OUT	Differential complementary clock output.			
24	vOE2#	IN	Active low input for enabling output 2. This pin has an internal 120kohm pull-down.			
24	VOE2#	IIN	1 = disable outputs, 0 = enable outputs.			
25	VDDO1.8	PWR	Power supply for outputs, nominally 1.8V.			
26	GND	GND	Ground pin.			
27	DIF3	OUT	Differential true clock output.			
28	DIF3#	OUT	Differential complementary clock output.			
20	VOE2#	INI	Active low input for enabling output 3. This pin has an internal 120kohm pull-down.			
29	vOE3#	IN	1 = disable outputs, 0 = enable outputs.			
30	GND	GND	Ground pin.			
			Input notifies device to sample latched inputs and start up on first high assertion.			
31	^CKPWRGD_PD#	IN	Low enters Power Down Mode, subsequent high assertions exit Power Down			
			Mode. This pin has internal 120kohm pull-up resistor.			
00			Tri-level latch to select SMBus Address. It has an internal 120kohm pull up			
32	^SADR_tri	LATCHED IN	resistor. See SMBus Address Selection Table.			
1						

Test Loads



Alternate Terminations

The 9DBV0541 can easily drive LVPECL, LVDS, and CML logic. See <u>"AN-891 Driving LVPECL, LVDS, and CML Logic with IDT's</u> <u>"Universal" Low-Power HCSL Outputs</u>" for details.

Absolute Maximum Ratings

Stresses above the ratings listed below can cause permanent damage to the 9DBV0541. These ratings, which are standard values for IDT commercially rated parts, are stress ratings only. Functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods can affect product reliability. Electrical parameters are guaranteed only over the recommended operating temperature range.

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	МАХ	UNITS	NOTES
Supply Voltage	VDDx	Applies to all VDD's	-0.5		2.5	V	1,2
Input Voltage	V _{IN}		-0.5		V _{DD} +0.5	V	1,3
Input High Voltage, SMBus	VIHSMB	SMBus clock and data pins			3.6	V	1
Storage Temperature	Ts		-65		150	°C	1
Junction Temperature	Tj				125	°C	1
Input ESD Protection	ESD prot	Human Body Model	2000			V	1

¹ Guaranteed by design and characterization, not 100% tested in production.

² Operation under these conditions is neither implied nor guaranteed.

³ Not to exceed 2.5V.

Electrical Characteristics–Clock Input Parameters

 $TA = T_{COM}$ or T_{IND} ; Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Input Crossover Voltage - DIF_IN	V _{CROSS}	Cross over voltage	150		900	mV	1
Input Swing - DIF_IN	V _{SWING}	Differential value	300			mV	1
Input Slew Rate - DIF_IN	dv/dt	Measured differentially	0.4		8	V/ns	1,2
Input Leakage Current	I _{IN}	$V_{IN} = V_{DD}$, $V_{IN} = GND$	-5		5	μA	
Input Duty Cycle	d_{tin}	Measurement from differential waveform	40		60	%	1
Input Jitter - Cycle to Cycle	J_{DIFIn}	Differential measurement	0		125	ps	1

¹ Guaranteed by design and characterization, not 100% tested in production.

² Slew rate measured through +/-75mV window centered around differential zero.

Electrical Characteristics–Input/Supply/Common Parameters–Normal Operating Conditions

 $TA = T_{COM}$ or T_{IND} ; Supply voltages per normal operation conditions; see Test Loads for loading conditions

TA = TCOM of TIND, Output vo	nages per i	ionnal operation conditions, see rest Loads for loadin	ig conditions)			
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Supply Voltage	VDDx	Supply voltage for core and analog	1.7	1.8	1.9	V	
Ambient Operating	T _{COM}	Commercial range	0	25	70	°C	1
Temperature	T _{IND}	Industrial range	-40	25	85	°C	1
Input High Voltage	V _{IH}	Single-ended inputs, except SMBus	$0.75 V_{DD}$		$V_{DD} + 0.3$	V	
Input Mid Voltage	VIM	Single-ended tri-level inputs ('_tri' suffix)	0.4 V _{DD}		0.6 V _{DD}	V	
Input Low Voltage	VIL	Single-ended inputs, except SMBus	-0.3		0.25 V _{DD}	V	
	I _{IN}	Single-ended inputs, V _{IN} = GND, V _{IN} = VDD	-5		5	μA	
Input Current	I _{INP}	Single-ended inputs $V_{IN} = 0 V$; inputs with internal pull-up resistors $V_{IN} = VDD$; inputs with internal pull-down resistors	-200		200	μA	
Input Frequency	F _{in}		1		200	MHz	2
Pin Inductance	L _{pin}				7	nH	1
	C _{IN}	Logic Inputs, except DIF_IN	1.5		5	pF	1
Capacitance	C_{INDIF_IN}	DIF_IN differential clock inputs	1.5		2.7	pF	1,6
	C _{OUT}	Output pin capacitance			6	pF	1
Clk Stabilization	T _{STAB}	From V _{DD} power-up and after input clock stabilization or de-assertion of PD# to 1st clock		1	ms	1,2	
Input SS Modulation Frequency PCIe	f _{MODINPCIe}	Allowable frequency for PCIe applications (Triangular modulation)	30		33	kHz	
Input SS Modulation Frequency non-PCIe	f _{MODIN}	Allowable frequency for non-PCIe applications (Triangular modulation)	0		66	kHz	
OE# Latency	t _{LATOE#}	DIF start after OE# assertion DIF stop after OE# deassertion	1		3	clocks	1,3
Tdrive_PD#	t _{DRVPD}	DIF output enable after PD# de-assertion			300	μs	1,3
Tfall	t _F	Fall time of single-ended control inputs			5	ns	2
Trise	t _R	Rise time of single-ended control inputs			5	ns	2
SMBus Input Low Voltage	VILSMB	$V_{DDSMB} = 3.3V$, see note 4 for $V_{DDSMB} < 3.3V$			0.8	V	4
SMBus Input High Voltage	VIHSMB	$V_{DDSMB} = 3.3V$, see note 5 for $V_{DDSMB} < 3.3V$	2.1		3.3	V	5
SMBus Output Low Voltage	V _{OLSMB}	at I _{PULLUP}			0.4	V	
SMBus Sink Current	IPULLUP	at V _{OL}	4			mA	
Nominal Bus Voltage	V _{DDSMB}	Bus Voltage	1.7		3.6	V	
SCLK/SDATA Rise Time	t _{RSMB}	(Max VIL - 0.15V) to (Min VIH + 0.15V)			1000	ns	1
SCLK/SDATA Fall Time	t _{FSMB}	(Min VIH + 0.15V) to (Max VIL - 0.15V)			300	ns	1
SMBus Operating Frequency	f _{MAXSMB}	Maximum SMBus operating frequency			400	kHz	7

¹ Guaranteed by design and characterization, not 100% tested in production.

 $^{\rm 2}$ Control input must be monotonic from 20% to 80% of input swing.

³ Time from deassertion until outputs are > 200 mV.

 4 For V_{DDSMB} < 3.3V, V_{ILSMB} < = 0.35V_{DDSMB.}

 5 For V_{DDSMB} < 3.3V, V_{IHSMB} > = 0.65V_{DDSMB.}

⁶ DIF_IN input.

⁷ The differential input clock must be running for the SMBus to be active.

Electrical Characteristics–DIF Low Power HCSL Outputs

TA = T_{COM} or T_{IND}; Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS		TYP	MAX	UNITS	NOTES
Slew Rate	Trf	Scope averaging on, fast slew rate setting	1.6	2.6	4.3	V/ns	1,2,3
Siew hale	111	Scope averaging on, slow slew rate setting	1.2	2.0	3.2	V/ns	1,2,3
Slew Rate Matching	∆Trf	Slew rate matching, Scope averaging on		6	20	%	1,2,4
Voltage High	V _{HIGH}	Statistical measurement on single-ended signal	660	758	850		7
Voltage Low	V _{LOW}	using oscilloscope math function. (Scope averaging on)	-150	43	150	mV	7
Max Voltage	Vmax	Measurement on single ended signal using		775	1150	mV	7
Min Voltage	Vmin	absolute value. (Scope averaging off)	-300	12		IIIV	7
Vswing	Vswing	Scope averaging off	300	1428		mV	1,2
Crossing Voltage (abs)	Vcross_abs	Scope averaging off	250	391	550	mV	1,5
Crossing Voltage (var)	∆-Vcross	Scope averaging off		14	140	mV	1,6

¹Guaranteed by design and characterization, not 100% tested in production. $C_L = 2pF$.

² Measured from differential waveform.

³ Slew rate is measured through the Vswing voltage range centered around differential 0V. This results in a +/-150mV window around differential 0V.

⁴ Matching applies to rising edge rate for Clock and falling edge rate for Clock#. It is measured using a +/-75mV window centered on the average cross point where Clock rising meets Clock# falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations.

⁵ Vcross is defined as voltage where Clock = Clock# measured on a component test board and only applies to the differential rising edge (i.e. Clock rising and Clock# falling).

⁶ The total variation of all Vcross measurements in any particular system. Note that this is a subset of Vcross_min/max (Vcross absolute) allowed. The intent is to limit Vcross induced modulation by setting Δ -Vcross to be smaller than Vcross absolute.

⁷ 660mV Vhigh is the minimum when VDDIO is >= 1.05V + -5%. If VDDIO is < 1.05V + -5%, the minimum Vhigh will be VDDIOmin - 250mV. For example for VDDIO = 0.9V + -5%, VHIGHmin will be 860mV - 250mV = 610mV.

Electrical Characteristics–Current Consumption

 $TA = T_{COM}$ or T_{IND} ; Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
	I _{DDR}	VDDR at 100MHz		2	3	mA	
Operating Supply Current	I _{DDDIG}	VDDIG, all outputs at 100MHz		0.2	0.5	mA	
	I _{DDO}	VDDO1.8, all outputs at 100MHz		23	27	mA	
	IDDRPD	VDDR, CKPWRGD_PD# = 0		0.001	0.1	mA	2
Powerdown Current	IDDDIGPD	VDDDIG, CKPWRGD_PD# = 0		0.17	0.3	mA	2
	I _{DDOPD}	VDDO1.8, CKPWRGD_PD# = 0		0.4	0.8	mA	2

¹ Guaranteed by design and characterization, not 100% tested in production.

² Input clock stopped.

Electrical Characteristics–Output Duty Cycle, Jitter, Skew and PLL Characteristics

 $TA = T_{COM}$ or T_{IND} ; Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS		TYP	MAX	UNITS	NOTES
Duty Cycle Distortion	t _{DCD}	Measured differentially, at 100MHz		-0.1	1	%	1,3
Skew, Input to Output	t _{pdBYP}	V _T = 50%	1800	2342	3000	ps	1
Skew, Output to Output	t _{sk3}	V _T = 50%		37	50	ps	1,4
Jitter, Cycle to Cycle	t _{jcyc-cyc}	Additive Jitter		0.1	5	ps	1,2

¹ Guaranteed by design and characterization, not 100% tested in production.

² Measured from differential waveform.

³ Duty cycle distortion is the difference in duty cycle between the output and the input clock.

⁴ All outputs at default slew rate.

Electrical Characteristics–Phase Jitter Parameters

 $TA = T_{COM}$ or T_{IND} ; Supply voltages per normal operation conditions; see Test Loads for loading conditions

						INDUSTRY		
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	LIMIT	UNITS	Notes
	t _{jphPCleG1}	PCIe Gen 1		0.1	5	N/A	ps (p-p)	1,2,3,5
	+	PCIe Gen 2 Lo Band 10kHz < f < 1.5MHz		0.1	0.4	N/A	ps (rms)	1,2,3,4,5
	t _{jphPCleG2}	PCIe Gen 2 High Band 1.5MHz < f < Nyquist (50MHz)		0.01	0.4	N/A	ps (rms)	1,2,3,4
Additive Phase Jitter	t _{jphPCleG3}	PCIe Gen 3 (2-4MHz or 205MHz, CDR = 10MHz)		0.00	0.1	N/A	ps (rms)	1,2,3,4
	t _{jphSGMIIM0}	125MHz, 1.5MHz to 10MHz, -20dB/decade rollover < 1.5MHz, -40db/decade rolloff > 10MHz		165	200	N/A	fs (rms)	1,6
	t _{jphSGMIIM1}	125MHz, 12kHz to 20MHz, -20dB/decade rollover < 1.5MHz, -40db/decade rolloff > 10MHz		251	300	N/A	fs (rms)	1,6

¹ Guaranteed by design and characterization, not 100% tested in production.

² See http://www.pcisig.com for complete specs.

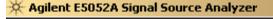
³ Sample size of at least 100K cycles. This figure extrapolates to 108ps pk-pk at 1M cycles for a BER of 1-12.

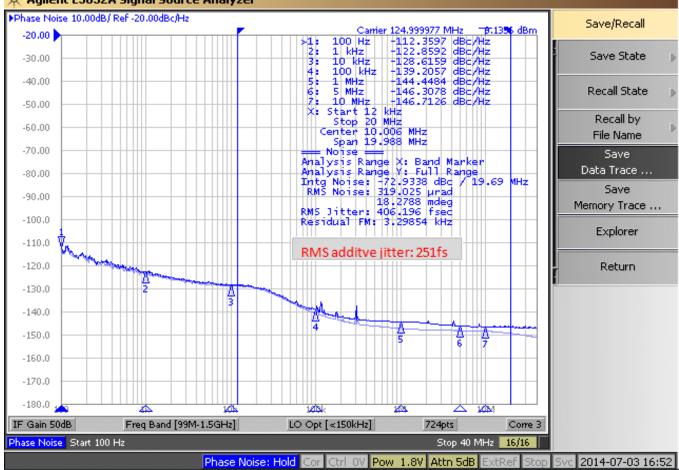
⁴ For RMS figures, additive jitter is calculated by solving the following equation: Additive jitter = SQRT[(total jitter)^2 - (input jitter)^2].

⁵ Driven by 9FGV0831 or equivalent.

⁶ Driven by Rohde & Schwarz SMA100.

Additive Phase Jitter Plot: 125M (12kHz to 20MHz)





General SMBus Serial Interface Information

How to Write

- Controller (host) sends a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) sends the byte count = X
- IDT clock will acknowledge
- Controller (host) starts sending Byte N through Byte N+X-1
- IDT clock will acknowledge each byte one at a time
- Controller (host) sends a stop bit

	Index Block Write Operation								
Controll	er (Host)		IDT (Slave/Receiver)						
Т	starT bit								
Slave A	Address								
WR	WRite								
			ACK						
Beginning	g Byte = N								
			ACK						
Data Byte	Count = X								
			ACK						
Beginnir	ng Byte N								
			ACK						
0		×							
0		X Byte	0						
0		Ð	0						
			0						
Byte N	+ X - 1								
			ACK						
Р	stoP bit								

Note: SMBus Address is Latched on SADR pin.

How to Read

- Controller (host) will send a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) will send a separate start bit
- Controller (host) sends the read address
- IDT clock will acknowledge
- IDT clock will send the data byte count = X
- IDT clock sends Byte N+X-1
- IDT clock sends Byte 0 through Byte X (if X_(H) was written to Byte 8)
- Controller (host) will need to acknowledge each byte
- Controller (host) will send a not acknowledge bit
- Controller (host) will send a stop bit

Index Block Read Operation						
Controller (Host)			IDT			
Т	starT bit					
SI	ave Address					
WR	WRite	_				
			ACK			
Begi	nning Byte = N	_				
			ACK			
RT	Repeat starT					
SI	ave Address					
RD	ReaD					
			ACK			
			Data Byte Count=X			
	ACK					
		_	Beginning Byte N			
	ACK					
		e	0			
	0	X Byte	0			
	0		0			
0						
			Byte N + X - 1			
Ν	Not acknowledge					
Р	stoP bit					

SMBus Table: Output Enable Register ¹

Byte 0	Name	Control Function	Туре	0	1	Default		
Bit 7	Reserved							
Bit 6	DIF OE3	Output Enable RW Low/Low OE# pin control				1		
Bit 5	DIF OE2	Output Enable	RW	Low/Low	OE# pin control	1		
Bit 4	Reserved							
Bit 3	DIF OE1	Output Enable	RW	Low/Low	OE# pin control	1		
Bit 2	Reserved							
Bit 1	DIF OE0	Output Enable	RW	Low/Low	OE# pin control	1		
Bit 0	Reserved							

1. A low on these bits will override the OE# pin and force the differential output Low/Low

SMBus Table: PLL Operating Mode and Output Amplitude Control Register

Byte 1	Name	Control Function	Туре	0	1	Default	
Bit 7	Reserved						
Bit 6	Reserved						
Bit 5	DIF OE4	Output Enable	RW	Low/Low	OE# pin control	1	
Bit 4	Reserved						
Bit 3	Reserved						
Bit 2	Reserved						
Bit 1	AMPLITUDE 1	Controls Output Amplitude	RW	00 = 0.6V	01 = 0.7V	1	
Bit 0	AMPLITUDE 0	Controis Output Amplitude	RW	10= 0.8V	11 = 0.9V	0	

1. A low on the DIF OE bit will override the OE# pin and force the differential output Low/Low

SMBus Table: DIF Slew Rate Control Register

Byte 2	Name	Control Function	Туре	0	1	Default		
Bit 7	Reserved							
Bit 6	SLEWRATESEL DIF3	Slew Rate Selection RW Slow setting Fast setting				1		
Bit 5	SLEWRATESEL DIF2	Slew Rate Selection	RW	Slow setting	Fast setting	1		
Bit 4	Reserved							
Bit 3	SLEWRATESEL DIF1	Slew Rate Selection	RW	Slow setting	Fast setting	1		
Bit 2	Reserved							
Bit 1	SLEWRATESEL DIF0	Slew Rate Selection	RW	Slow setting	Fast setting	1		
Bit 0		Reserved	Reserved					

SMBus Table: DIF Slew Rate Control Register

Byte 3	Name	Control Function	Туре	0	1	Default	
Bit 7	Reserved						
Bit 6	Reserved						
Bit 5		Reserved					
Bit 4	Reserved						
Bit 3	Reserved						
Bit 2	Reserved						
Bit 1	Reserved						
Bit 0	SLEWRATESEL DIF4	Adjust Slew Rate of DIF4	RW	Slow setting	Fast setting	1	

Byte 4 is Reserved

Byte 5	Name	Control Function	Туре	0	1	Default
Bit 7	RID3		R		0	
Bit 6	RID2	Revision ID	R	A rev =	0	
Bit 5	RID1		R	A lev -	0	
Bit 4	RID0		R			0
Bit 3	VID3		R			0
Bit 2	VID2	VENDOR ID	R	0001	0001 = IDT	
Bit 1	VID1	VENDOR ID	R	0001	0	
Bit 0	VID0]	R		1	

SMBus Table: Revision and Vendor ID Register

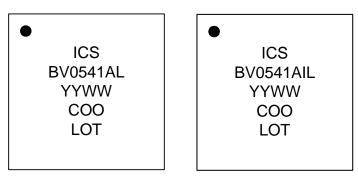
SMBus Table: Device Type/Device ID

Byte 6	Name	Control Function	Туре	0	1	Default	
Bit 7	Device Type1	Device Type	R	00 = FG,	1		
Bit 6	Device Type0	Device Type	R	10 = DM, 11=	1		
Bit 5	Device ID5		R			0	
Bit 4	Device ID4		R			0	
Bit 3	Device ID3	Device ID	R	000101 bipa	000101 binary or 05 hex		
Bit 2	Device ID2	Device ID	R	000101 011a			
Bit 1	Device ID1		R			0	
Bit 0	Device ID0		R				

SMBus Table: Byte Count Register

Byte 7	Name	Control Function	Туре	0	1	Default	
Bit 7	Reserved						
Bit 6	Reserved						
Bit 5	5 Reserved						
Bit 4	BC4		RW			0	
Bit 3	BC3		RW	Writing to this regist	er will configure how	1	
Bit 2	BC2	Byte Count Programming	RW	many bytes will be r	ead back, default is	0	
Bit 1	BC1]	RW	= 8 b	ytes.	0	
Bit 0	BC0		RW			0	

Marking Diagrams



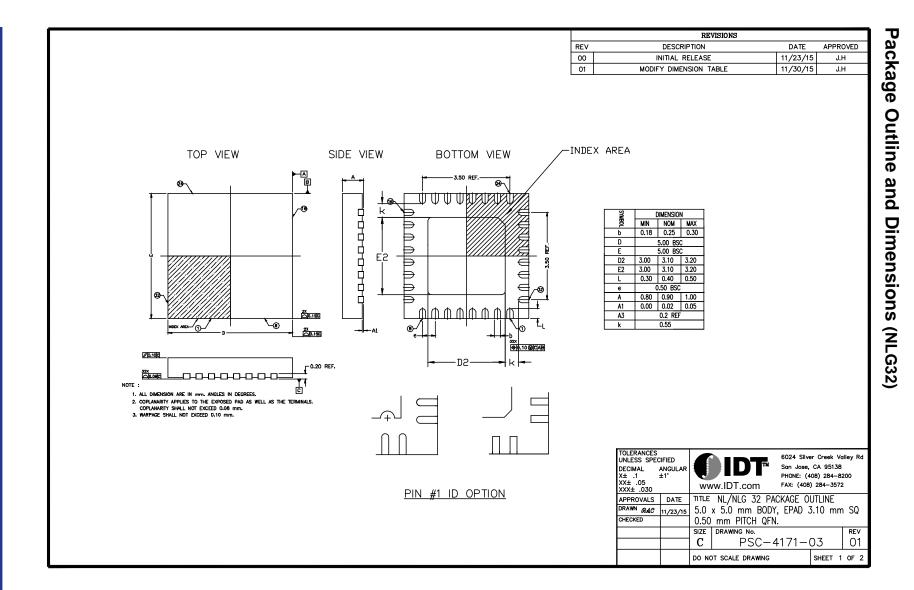
Notes:

- 1. "LOT" is the lot sequence number.
- 2. "COO" denotes country of origin.
- 3. YYWW is the last two digits of the year and week that the part was assembled.
- 4. Line 2: truncated part number
- 5. "L" denotes RoHS compliant package.
- 6. "I" denotes industrial temperature range device.

Thermal Characteristics

PARAMETER	SYMBOL	CONDITIONS	PKG	TYP VALUE	UNITS	NOTES
	θ _{JC}	Junction to Case			°C/W	1
	θ_{Jb}	Junction to Base		2.4	°C/W	1
Thermal Resistance	θ_{JA0}	Junction to Air, still air	NLG32	39	°C/W	1
mermai Resistance	θ_{JA1}	Junction to Air, 1 m/s air flow	INLG32	33	°C/W	1
	θ_{JA3}	Junction to Air, 3 m/s air flow		28	°C/W	1
	θ_{JA5}	Junction to Air, 5 m/s air flow		27	°C/W	1

¹ePad soldered to board



D

9DBV0541 DATASHEET

1	

Package
Outline and I
nd Dimensio
ns (I
NLG32), cont

	REV	DESCRIF	REVISIONS	DATE	APPROVED
	00	INITIAL RE		11/23/15	J.H
	01	MODIFY DIMEN		11/30/15	J.H
5.75 4.05 0.30 0.50 0.50 0.50 0.85 0.50 0.85 0.50 0.85 0.85 0.50 0.85 0.50 0.85 0.50 0.85 0.50 0.85 0.50 0					
RECOMMENDED LAND PATTERN.					
 NOTES: 1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES. 2. TOP DOWN VIEW. AS VIEWED ON PCB. 3. COMPONENT OUTLINE SHOWS FOR REFERENCE IN GREEN. 4. LAND PATTERN IN BLUE. NSMD PATTERN ASSUMED. 5. LAND PATTERN RECOMMENDATION PER IPC-7351B GENERIC REQUIREMENT FOR SURFACE MOUNT DESIGN AND LAND PATTERN. 	UNLE DECII X± XX± XXX± APPF	1 ±1° .05 ≈0.30 ROVALS DATE N <i>PXP</i> 12/20/06 KED	WWW.IDT.com TITLE NL/NLG 32 P/ 5.0 x 5.0 mm B0D 0.50 mm PITCH QFI SIZE DRAWING No. C PSC- DO NOT SCALE DRAWING	San Jose, C PHONE: (408 FAX: (408) 2 ACKAGE OUT Y, EPAD 3. N. 4171-0) 284–8200 284–3572 LINE 10 mm SQ REV

Ordering Information

Part / Order Number	nber Shipping Packaging Package Tempe		Temperature
9DBV0541AKLF	Trays	32-pin QFN	0 to +70° C
9DBV0541AKLFT	Tape and Reel	32-pin QFN	0 to +70° C
9DBV0541AKILF	Trays	32-pin QFN	-40 to +85° C
9DBV0541AKILFT	Tape and Reel	32-pin QFN	-40 to +85° C

"LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant. "A" is the device revision designator (will not correlate with the datasheet revision).

Revision History

D	RDW	5/23/2016	Updated package outline drawings with latest version from Doc Control.	14,15
E	RDW	3/10/2017	 Removed "Bypass Mode" reference in note 3 under Output Duty Cycle table. Corrected spelling errors/typos. Update Additive Phase Jitter conditions for PCIe Gen3. 	8
F	RDW	5/30/2017	1. Corrected marking diagram for I-temp device.	13
G	C. Chen	10/27/2017	Updated ordering information to align with package outline drawings code.	16



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